

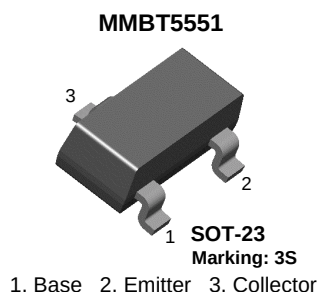


2N5551- MMBT5551

NPN General Purpose Amplifier

Features

- This device is designed for general purpose high voltage amplifiers and gas discharge display drivers.
- Suffix "-C" means Center Collector in 2N5551 (1. Emitter 2. Collector 3. Base)
- Suffix "-Y" means h_{FE} 180~240 in 2N5551 (Test condition : $I_C = 10mA$, $V_{CE} = 5.0V$)



Absolute Maximum Ratings * $T_a = 25^\circ C$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{CEO}	Collector-Emitter Voltage	160	V
V_{CBO}	Collector-Base Voltage	180	V
V_{EBO}	Emitter-Base Voltage	6.0	V
I_C	Collector current - Continuous	600	mA
T_J, T_{stg}	Junction and Storage Temperature	-55 ~ +150	$^\circ C$

* These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1. These ratings are based on a maximum junction temperature of 150 degrees C.
2. These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics $T_a = 25^\circ C$ unless otherwise noted

Symbol	Parameter	Max		Units
		2N5551	*MMBT5551	
P_D	Total Device Dissipation Derate above $25^\circ C$	625 5.0	350 2.8	mW mW/ $^\circ C$
$R_{\theta JA}$	Thermal Resistance, Junction to Case	83.3		$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	357	$^\circ C/W$

* Device mounted on FR-4 PCB $1.6'' \times 1.6'' \times 0.06''$

Electrical Characteristics $T_a = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
Off Characteristics					
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage *	$I_C = 1.0\text{mA}, I_B = 0$	160		V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 100\mu\text{A}, I_E = 0$	180		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 10\mu\text{A}, I_C = 0$	6.0		V
I_{CBO}	Collector Cutoff Current	$V_{CB} = 120\text{V}, I_E = 0$ $V_{CB} = 120\text{V}, I_E = 0, T_a = 100^\circ\text{C}$		50 50	nA μA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = 4.0\text{V}, I_C = 0$		50	nA
On Characteristics					
h_{FE}	DC Current Gain	$I_C = 1.0\text{mA}, V_{CE} = 5.0\text{V}$ $I_C = 10\text{mA}, V_{CE} = 5.0\text{V}$ $I_C = 50\text{mA}, V_{CE} = 5.0\text{V}$	80 80 30	250	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 10\text{mA}, I_B = 1.0\text{mA}$ $I_C = 50\text{mA}, I_B = 5.0\text{mA}$		0.15 0.20	V V
$V_{BE(sat)}$	Base-Emitter On Voltage	$I_C = 10\text{mA}, I_B = 1.0\text{mA}$ $I_C = 50\text{mA}, I_B = 5.0\text{mA}$		1.0 1.0	V V
Small Signal Characteristics					
f_T	Current Gain Bandwidth Product	$I_C = 10\text{mA}, V_{CE} = 10\text{V},$ $f = 100\text{MHz}$	100	300	MHz
C_{obo}	Output Capacitance	$V_{CB} = 10\text{V}, I_E = 0, f = 1.0\text{MHz}$		6.0	pF
C_{ibo}	Input Capacitance	$V_{BE} = 0.5\text{V}, I_C = 0, f = 1.0\text{MHz}$		20	pF
H_{fe}	Small-Signal Current Gain	$I_C = 1.0\text{mA}, V_{CE} = 10\text{V}, f = 1.0\text{kHz}$	50	250	
NF	Noise Figure	$I_C = 250\mu\text{A}, V_{CE} = 5.0\text{V},$ $R_s = 1.0\text{k}\Omega, f = 10\text{Hz to } 15.7\text{kHz}$		8.0	dB

Spice Model

NPN (Is=2.511f Xti=3 Eg=1.11 Vaf=100 Bf=242.6 Ne=1.249 Ise=2.511f Ikf=.3458 Xtb=1.5 Br=3.197 Nc=2 Isc=0 Ikr=0 Rc=1 Cjc=4.883p Mjc=.3047 Vjc=.75 Fc=.5 Cje=18.79p Mje=.3416 Vje=.75 Tr=1.202n Tf=560p Itf=50m Vtf=5 Xtf=8 Rb=10)

Typical Performance Characteristics

Figure 1. Typical Pulsed Current Gain vs Collector Current

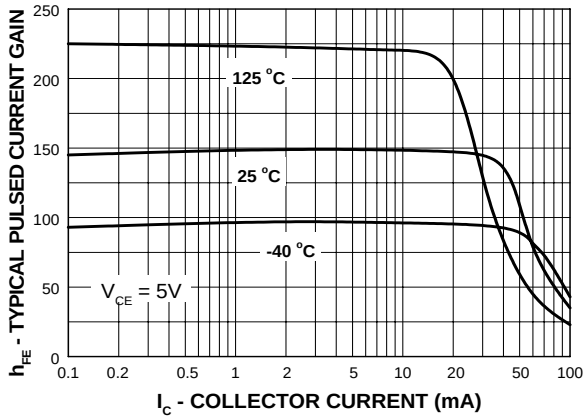


Figure 2. Collector-Emitter Saturation Voltage vs Collector Current

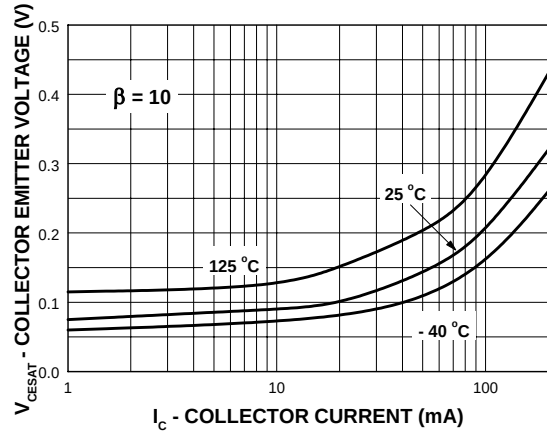


Figure 3. Base-Emitter Saturation Voltage vs Collector Current

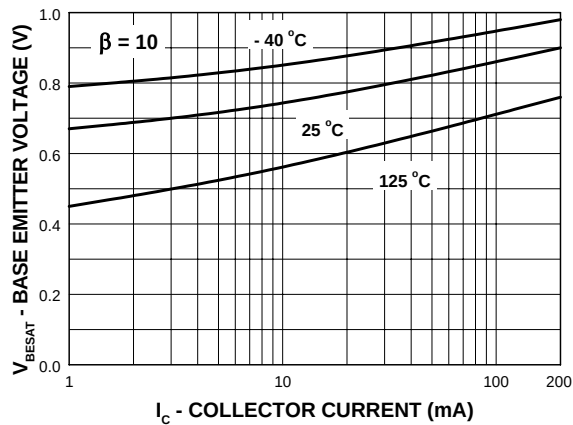


Figure 4. Base-Emitter On Voltage vs Collector Current

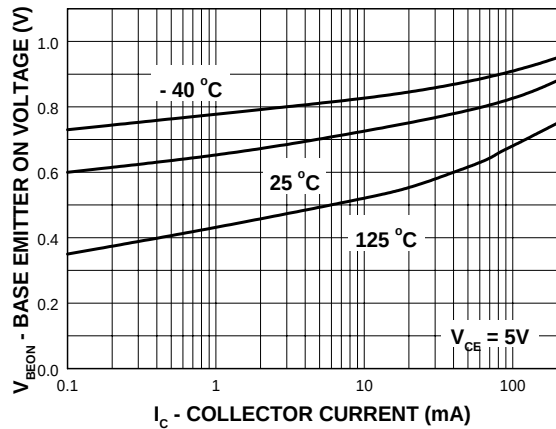


Figure 5. Collector Cutoff Current vs Ambient Temperature

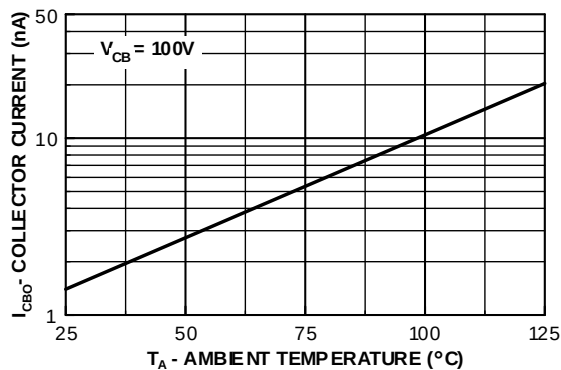
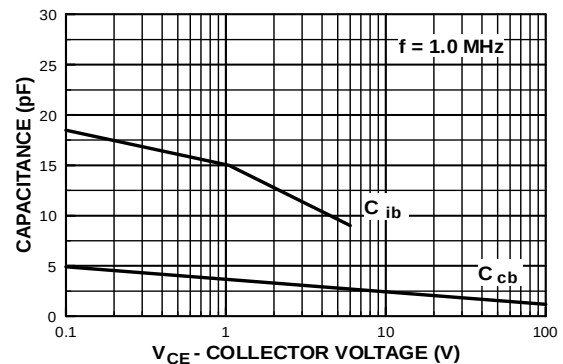


Figure 6. Input and Output Capacitance vs Reverse Voltage



Typical Performance Characteristics (Continued)

Figure 7. Collector- Emitter Breakdown Voltage with Resistance Between Emitter-Base

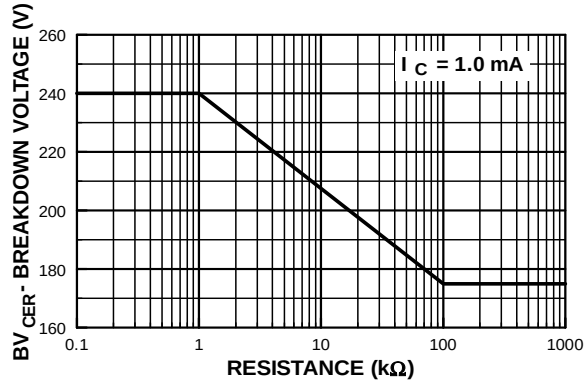


Figure 8. Small Signal Current Gain vs Collector Current

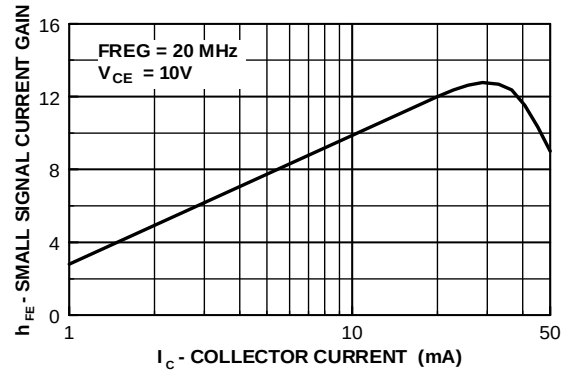
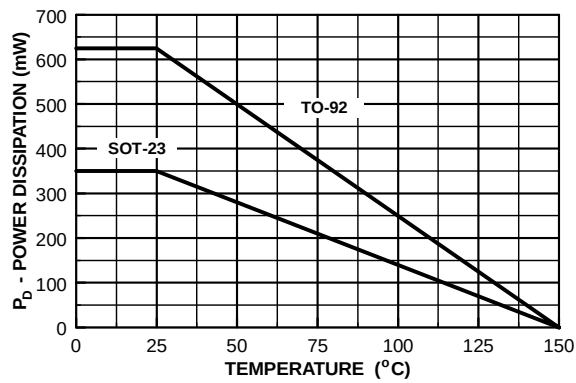


Figure 9. Power Dissipation vs Ambient Temperature



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